Contribution to the soap "wild and romantic physics ":

AENEAS

Aluminum-based Extreme-field Normal-conducting Electron Accelerating Structure

Wolfgang Hillert

Aeneas' Traum

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Aluminum-based Extreme-field Normal-conducting Electron Accelerating Structure

Contents:

- TW and SW Linac structures
- ultra-pure aluminium at low temperatures
- concepts for a Linac made from aluminium
- first measurements
 - outlook

Aeneas' Traum

TW and SW Linac structures



Abreise von Aeneas und seiner Familie von Troja

Travelling Waves in an iris-loaded Waveguide (Runzelröhre)



Energy diffusion equation:

$$\frac{\partial P}{\partial t} + \frac{\partial P}{\partial s} + P_w + \frac{\partial P}{\partial s} = 0$$

where:	W	=	stored energy per unit length,
	Р	=	energy flux along s,
	$P_{ m w}$	=	wall losses per unit length,
	$I_b E_{\parallel}$	=	energy transferred to the beam.

Travelling Waves in the Runzelröhre



Parameters and their link:

$$Q = \frac{\omega W}{P_W}, \qquad P_W = \frac{\ddot{E}_{\parallel}^2}{r_S}$$

Energy flux along the structure, damping length:

$$P = \mathbf{v}_g \cdot W \qquad \qquad l_0 = \frac{2\mathbf{v}_g Q}{\omega}$$

Energy dissipation:

$$P_{W} = \frac{\omega}{\mathbf{v}_{g}Q} \cdot W \cdot \mathbf{v}_{g} = \frac{\omega}{\mathbf{v}_{g}Q} \cdot P = \frac{2}{l_{0}} \cdot P$$

Travelling Waves in the Runzelröhre



Acc. field E_{\parallel} does not depend on electrical properties of material!!!

Constant Gradient Structure:



Energy diffusion equation with beam loading:

$$\frac{\partial P}{\partial t} + \frac{\partial P}{\partial s} + P_w + I_b E_{\parallel} = 0$$

After ,,lengthy" calculations (c.f. script of lecture acc. physics):

$$E_{\parallel}(s) = E_0 + \frac{1}{2}r_s I_b \cdot \ln\left\{1 - \frac{s}{L}\left(1 - e^{-2\tau}\right)\right\}$$



Compensation of beam loading:

 \rightarrow dedicated RF drive!

CLIC PULSE SHAPE OPTIMIZATION





U-----

Standing Waves in the Fridge



Dynamics determined completely by beam loading:

Optimum coupling:

$$\kappa_{opt} = 1 + \frac{P_{beam}}{P_{wall}}$$

"hopeless" overcritical coupled!

 $(1+\kappa)\omega_0$

<u>The high κ approach</u>:

- Typical quality factors $Q \approx 10^{10} \rightarrow$ resonance width ca. 0.1 Hz!!!
- $R_{\rm s}$ comes for free, therefore optimization for low crit. fields
- Strong overcritical coupling causes many advantages:
 - broad resonance curve by ext. loading / Q_{ext} of typ. 10⁵ 10⁶
 - no influence on dissipation, $R_{\rm S}$ remains unchanged
 - no reflection when operating with design beam current
 - reduction of structure filling time: $\tau = \frac{Q_l}{\tau} = \frac{Q_0}{\tau}$

Fill Times \leftrightarrow **Pulse Lengths**



Ultra-pure Aluminium at low Temperatures

Herr Hillert! Bei tiefen Temperaturen taugt Reinstaluminium mehr als der beste Supraleiter!

Das war ja dann wohl nichts mit 100MV/m und Supraleitern ...

Aeneas flicht aus Troja

Die Leitfähigkeit eines freien Elektronengases in einem Phononenbad nach der statistischen Thermodynamik irreversibler Prozesse

Von Rudolf Klein

Aus dem Institut für Theoretische Physik der Technischen Hochschule Braunschweig (Z. Naturforschg. 18 a, 1351–1359 [1963]; eingegangen am 3. Oktober 1963)

The formulation of the many-body problem by MARTIN and SCHWINGER is applied to a system of free electrons interacting with a phonon bath. Simplifying the general expression for the wave vector and frequency dependent complex conductivity to the case of a static dc situation the conductivity is expressed in terms of the LAPLACE transform of an appropriate GREEN's function. By means of a simple diagram method a transport equation for this function is derived. In the lowest approximation the solution of this equation gives the BLOCH-GRÜNEISEN law for the conductivity of metals at low temperatures.

In der bekannten Theorie der elektrischen Leitfähigkeit in Metallen benutzt man die BOLTZMANN-Gleichung. Die Herleitung dieser Gleichung enthält wichtige Annahmen¹, den "Stoßzahlansatz", bzw. in der quantenmechanischen Behandlung die "repeated random phase approximation", sowie die Voraussetzung der schwachen Kopplung zwischen Elektronen und Gitter.

Aus diesen Gründen hat man versucht, die elektrische Leitfähigkeit auf andere Weise zu behan-

¹ R. E. PEIERLS, The Quantum Theory of Solids, Clarendon Press, Oxford 1955. deln, zum Teil, um zu sehen, in welcher Näherung einer allgemeinen Theorie die früher hergeleiteten Ergebnisse herauskommen, und zum anderen, um neue Ausdrücke für die Leitfähigkeit zu bekommen, die nicht auf den Fall schwacher Kopplung beschränkt sind. Diese enthalten die Kopplungskonstanten in höheren Potenzen. So leiteten KOHN und LUTTINGER² die BOLTZMANN-Gleichung aus der Bewegungsgleichung für die Dichtematrix her und zeigten im Fall elastischer Streuung an Verunreini-

² W. KOHN u. J. A. LUTTINGER, Phys. Rev. 108, 590 [1957].

From R. Klein, last Pages:

Dazu tritt noch die Lösung der homogenen Gleichung. Man macht sich leicht klar, daß diese Lösung zur Leitfähigkeit nichts beiträgt, ganz analog zu der Situation bei der Behandlung dieses Problems mit Hilfe einer die BOLTZMANN-Gleichung erfüllenden Verteilungsfunktion.

Damit ist

$$\sigma = \frac{e^2 \beta}{6 m^2} \sum_{p} p^2 n_p n_{\overline{p}} \tau(p) + \text{k. k.}$$
(61)

Diesen Ausdruck bringt man leicht auf die bekannte Form

$$\sigma = \frac{e^2 n}{m} \tau(p_0) , \qquad (62)$$

wo p_0 der FERMI-Impuls und n die Anzahl der Elektronen pro cm³ ist. Dabei macht man Gebrauch von

$$F(p_0) = -\int_0^\infty d\mathbf{p} \,\frac{\partial n_p}{\partial p} \,F(p) = \frac{2 \,\pi^2 \,\beta}{m} \sum_p n_p \,n_p^- \,\frac{1}{p} \,F(p)\,,$$
(63)

wobei $\partial n_p / \partial p$ in der ersten Gleichung als reine δ -Funktion angesehen wird und F(p) eine stetige Funktion ist. Wir wollen $\tau(p_0)$ berechnen, um das so entstandenen Gleichung für $1/\tau(p_0)$ werden in Integrale verwandelt. Das Integral über p ist einfach, da die Faktoren $n_p n_{p+k}$ und $n_{p+k} n_p \delta$ -funktionsartig sind. Das Integral über k ist unter der Berücksichtigung von $g^2(\mathbf{k}) \sim |\mathbf{k}|$ proportional dem auch bei SOMMERFELD und BETHE¹⁴ auftretenden Integral

$$J_5\left(\frac{\Theta}{T}\right) = \int_0^{\Theta/T} \frac{\eta^5 \,\mathrm{d}\eta}{(e^\eta - 1) \,(1 - e^{-\eta})}$$

Auf diese Weise ergibt sich schließlich

$$\tau(p_0) = \frac{9 \, M \, N \, \pi \, p_0{}^3 \, s^6}{m \, C^2 (k_{\rm B} \, T){}^5 \, J_5(\Theta/T)} \,,$$

was mit Gl. (62)gerade das BLOCH-GRÜNEISEN-Gesetz darstellt.

Die hier hergeleitete Transportgleichung, die das bekannte Widerstandsverhalten liefert, ist prinzipiell einfach auszudehnen auf den Fall der frequenzabhängigen Leitfähigkeit und andererseits auch auf höhere Näherungen in der Kopplung, wo man also

¹⁴ A. SOMMERFELD u. H. BETHE, Handbuch der Physik, Bd. 24, Teil II, Springer-Verlag, Berlin 1933.

Resistance from Grüneisen Law





Desillusion 1st Part

Key Parameters for Accelerating Structures

Quick scan of textbook literature:

- Skin depth:
- Surface resistance:
- Quality factor:
- Shunt impedance:

$\delta = \sqrt{\frac{2}{\mu_0 \omega_0 \sigma}} \approx 7,5 \text{nm} @ 6 \text{GHz & } 4 \text{K}$								
$R_{sf} = \frac{1}{\sigma\delta} = \sqrt{\frac{\mu_0 \omega_0}{2\sigma}}$ scales with the square root!!!								
$Q_0 = \frac{j_0 \cdot Z_0}{2R_{sf} \left(1 + \frac{r}{L}\right)}, \text{with}: Z_0 = \sqrt{\frac{\mu_0}{\varepsilon_0}}, r = \text{radius}, L = \text{length}$								
$R_{s} = 2 \frac{\left(Z_{0} \cdot L\right)^{2}}{\pi^{3} \cdot r^{2} \cdot R_{sf} \cdot J_{1}(j_{0}) \cdot \left(1 + \frac{L}{R}\right)}$								

However: a factor > 100 remains! No *H*_C**!!!**

Useful Approaches

Wie wäre es denn mit Seitenkopplung?

Das ist ja großer Mist mit den Füllzeiten!

Venus zeigt Aeneas Waffen

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PARALLEI. COUPLED CAVITY STRUCTURE*

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Summary

A parallel coupled RF cavity structure which provides favorable solutions to all of the requirements for use in an e⁺e⁻ storage ring is described. Properties of this structure have been determined mathematically and through measurements on S-band models. An L-band prototype is being constructed and will be tested at high power.

Introduction

An RF cavity structure suitable for use in Cornell's proposed CESR e⁺e⁻ storage ring must satisfy a number of requirements. These are summarized in Table I.

TABLE I STRUCTURE REQUIREMENTS

Operate at 500 MHz Maximize shunt impedance in the available space (four spaces, 6 meters each) Minimize number of separately powered modules Avoid passband mode overlap Minimize sensitivity of amplitude and phase to individual cell frequency errors Obtain intrinsic thermal stability Provide adequate cooling Provide simple means for tuning the structure to compensate for loading by the beam Provide sufficient loading of all important TM₀ and TM₁ modes to prevent cavity-induced instabilities shows the equivalent circuit of the structure. All cells, shown as R, L, and C, are effectively in series with the coupling line at half-wavelength intervals. The coupling iris adds an effective inductance L' in series with each cell.



Fig. 1. Parallel coupled cavity structure, including water tank used for cooling.



PARALLEL-COUPLED ACCELERATING STRUCTURES

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Figure 2. Scheme of the accelerating structure. 1 - accelerating cavity, 2 - capacity protuberance, 3 coupling slot, 4 - symmetrized magnetic circuit, 5 magnets, 6 – transmission-type cavity, 7 – input coupling hole.

The accelerating cavities (1) are excited from the transmission-type cavity (6) through coupling slots (3) in the common wall. Excitation of the whole system is carried out through a coupling hole (7). The transmissiontype cavity (6) represents a cut of the rectangular waveguide, operated on H_{104} -mode. The wave-guide is loaded with rectangular feeding waveguides.



LINAC'02



Aluminum-based Extreme-field Normal-conducting Electron Accelerating Structure



$$\Lambda = 2\lambda \qquad \Leftrightarrow \qquad \lambda = \sqrt{3} \cdot a, \quad \mathbf{v}_{ph} = 2c, \quad \mathbf{v}_g = 0.5c, \quad Z = 2Z_{vac}$$

HOM Suppression?!



Figure 4.24: Cutaway view of (a) upstream end of RDDS1 and (b) RDDS1 cell.

HOM Forward Damping

Free choice of waveguide height *b* for TE₁₀!

Idea: cancelling of dipole mode via coupling to TM₁₁!

<u>Resonance frequencies</u>: $f_1 = j_1/j_0 \cdot f_0$

- fundamental mode: $k_c r = j_0 = 2,405$
- dipole mode: $k_c r = j_1 = 3,83$

Cancelling after *n* resonators:

$$\mathbf{v}_{ph,1} = \frac{c}{\sqrt{1 - \left(\frac{j_o}{n \cdot j_1}\right)}}, \qquad \text{cut-off: } \frac{1}{\lambda_c} = \frac{1}{2}\sqrt{\frac{1}{a^2}}$$

After brave calculations:

$$\frac{b}{a} = \frac{3}{4} \cdot \left[\frac{2}{n} \cdot \frac{j_1}{j_0} - \frac{1}{n^2}\right]^{-1}$$



4 cm !!!

Machining Tolerances / Temperature

(why are side-coupled structures not used so far?)

Tolerances:

a) Standing wave structures:

$$\frac{\omega}{c}r = j_0, \quad \tan \varphi = Q_0 \cdot \left(\frac{\omega_0}{\omega} - \frac{\omega}{\omega_0}\right), \quad \frac{\omega}{\omega_0} = \frac{r_0}{r} \quad \Rightarrow \quad \left| \Delta \varphi = 2Q \cdot \frac{\Delta r}{r_0} \cdot \left\{ 1 + 4Q^2 \left(\frac{\Delta r}{r_0}\right)^2 \right\}^{-1} \right|$$

for
$$Q \approx 10^4$$
 we get:

4	$\Delta r/r$	10-6	10 -5	10-4	$12 \text{ GHz} (r \approx 10 \text{ mm}) \rightarrow$	$\Delta r = 10 \text{ nm}!!$
Δ¢	ø/ deg	1,1 °	11 °	29 °		

b) Travelling wave structures:

phase advance: $\varphi = 2\pi d/\lambda \rightarrow \Delta \varphi = d \cdot \Delta k$ und $\Delta k = dk/d\omega \cdot \Delta \omega = \Delta \omega/v_g$ gives $12 \text{ GHz}, v_g \approx 0.01 \ d = \lambda/3$

es $\frac{d\varphi}{dr} = \frac{d\omega}{dr} \cdot \frac{d}{v_g}$ $12 \text{ GHz, } v_g \approx 0.01 \quad d = \lambda/3$ $\Delta r = 1 \text{ } \mu \text{m}$

Machining Tolerances / Temperature

(why are side-coupled structures not used so far?)

Temperature:

Requirement for CLIC: $\Delta T < 0.1^{\circ}C \leftrightarrow \Delta E/E < 0.05\%$

Temperatur change will detune all cavities in the same way!

General relationship:

$$\frac{\Delta E}{E} = \tan \varphi \cdot \Delta \varphi + \frac{1}{2} \Delta \varphi^2$$

Gives for required $\Delta E/E$

$$\Delta \phi = 1,3^{\circ} @ \cos(\phi = 0^{\circ})$$

 $\Delta \phi = 0,1^{\circ} @ \cos(\phi = 8^{\circ})$

and for
$$\Delta r/r = 2.31 \cdot 10^{-5} \cdot \Delta T$$

 $\Delta T < 0.005 \text{ K} \leftrightarrow \Delta P < 5 \text{ mbar}$



Thermal Expansion Coefficient

K. Anders: Thermische Ausdehnung von Metallen bei tiefen Temperaturen, Phys. kond. Mat. 2 (1964)



First Measurements

Probieren geht über studieren!

Venus erscheint Aeneas und Achates

Simple Set Up of a "He Cryostat"



- Slit coupling of resonator !
- Waveguide with coax transitions!



temperature / K



quality factor QO

frequency / GHz

temperature / K



frequency / GHz

Desillusion 2nd Part and Upcoming Sadness

Verzweiflung, Wut und Schrecken, begleiten ihren Fall ...

Aeneas besiegt den Turnus

Anomalous Skin Effect



Implications

W. Chou, F. Ruggiero: Anomalous Skin Effect and Resistive Wall Heating, LHC Project Note 2 (SL/AP), Geneva 9/8/1995

Increase of surface resistance according to:

$$R_{sf} = \frac{1}{\sigma \cdot \delta} \quad \rightarrow \quad R_{sf} = R_{\infty} \cdot \left(1 + 1.157 \alpha^{-0.276}\right) \quad \text{für} \quad \alpha \ge 3$$

where:

$$\alpha = \frac{3}{2} \left(\frac{\lambda}{\delta}\right)^2 = \frac{3}{4} \omega \mu_0 \left(\lambda\sigma\right)^2 \quad und \quad R_{\infty} = \sqrt[3]{\frac{\sqrt{3}}{16\pi} \cdot \frac{\lambda}{\sigma} \cdot \left(\omega\mu_0\right)^2} = \frac{1}{\sigma \cdot \delta} \cdot \sqrt[3]{\frac{\lambda}{4\pi}} \frac{\lambda}{\delta}$$

Unknown "material parameter" λ/σ with $(\lambda/\sigma)_{Cu} = 6.6 \cdot 10^{-16} \Omega m^2$ taken from

- A.F. Mayadas: Intrinsic Resistivity and Electron Mean Free Path in Aluminium Films, J. Appl. Phys. 39,9 (1965)
- J.C. Ashley et al.: *Electron inelastic mean free paths and energy losses in solids*, Surf. Sci. **81** (1979)

Conservative guess: $(\lambda/\sigma)_{Al} = 7 \cdot 10^{-16} \Omega m^2$!

Normal und Anomalous Skin Effect



Sputtering of thin surface films < 10nm indispensable to oversome the anomalous skin effect^{ommt, ihr} Töchter, helft mir klagen ... but:

Outloo

does this work and really help? high risk, high fun – high gain???

Für einen Faktor <30 lohnt der Aufwand nicht...?